



HF125-28

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI HF125-28 is Designed for

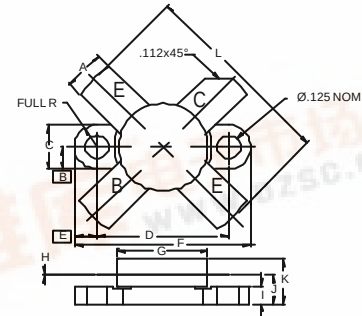
FEATURES:

- $P_G = 15$ dB min. at 100 W/30 MHz
- $IMD_3 = -30$ dBc max. at 100 W_(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	20 A
V_{CBO}	65 V
V_{CEO}	36 V
V_{EBO}	4.0 V
P_{DISS}	270 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$0.65^\circ C/W$

PACKAGE STYLE .500 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B		.125 / 3.18
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.730 / 18.54
E		.125 / 3.18
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K		.280 / 7.11
L	.980 / 24.89	1.050 / 26.67

ORDER CODE: ASI10608

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS				MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100$ mA				35			V
BV_{CES}	$I_C = 100$ mA				65			V
BV_{CBO}	$I_C = 100$ mA				65			
BV_{EBO}	$I_E = 10$ mA				4.0			V
I_{CES}	$V_{CE} = 30$ V						15	mA
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 5.0$ A			10		200	---
C_{ob}	$V_{CB} = 30$ V	$f = 1.0$ MHz			---	250	---	pF
G_p	$V_{CE} = 28$ V	$P_{IN} = 3.95$ W	$f = 30$ MHz		15	16		dB
IMD_3	$V_{CE} = 28$ V	$I_{CQ} = 100$ mA	$f = 30$ MHz			-34	-30	dBc